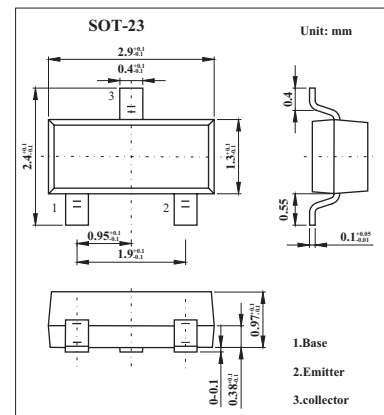


General Purpose Transistor

BCW61A/B/C/D

■ Features

- PNP Epitaxial Silicon Transistor

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-32	V
Collector-Emitter Voltage	V_{CE0}	-32	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Storage Temperature	T_{STG}	-55 to +150	$^\circ\text{C}$

BCW61A/B/C/D

■ Electrical Characteristics Ta = 25°C

Parameter		Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current		ICBO	IE = 0; VCB = -32 V			-20	nA
		ICBO	IE = 0; VCB = -32 V; Tamb = 150 °C			-20	μA
Emitter cutoff current		IEBO	IC = 0; VEB = -4 V			-20	nA
DC current gain	BCW61B	hFE	IC = -10 μA; VCE = -5 V	30			
	BCW61C			40			
	BCW61D			100			
DC current gain	BCW61B	hFE	IC = -2 mA; VCE = -5 V	180		310	
	BCW61C			250		460	
	BCW61D			380		630	
DC current gain	BCW61B	hFE	IC = -50 mA; VCE = -5 V	80			
	BCW61C			100			
	BCW61D			110			
Collector-emitter saturation voltage		VCE(sat)	IC = -10 mA; IB = -0.25 mA	-60		-250	mV
			IC = -50 mA; IB = -1.25 mA	-120		-550	mV
Base to emitter saturation voltage		VBE(sat)	IC = -10 mA; IB = -0.25 mA	-600		-850	mV
			IC = -50 mA; IB = -1.25 mA	-0.68		-1.05	V
Base to emitter voltage		VBE	IC = -2 mA; VCE = -5 V	-600	-650	-750	mV
Collector capacitance		Cc	IE = ie = 0; VCB = -10 V; f = 1 MHz		4.5		pF
Emitter capacitance		Ce	IC = ic = 0; VEB = -0.5 V; f = 1 MHz		11		pF
Transition frequency *		fT	IC = -10 mA; VCE = -5 V; f = 100 MHz	100			MHz
Noise figure		NF	IC = -200 μA; VCE = -5 V; Rs = 2 kΩ; f = 1 kHz; B = 200 Hz		2	6	dB

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

TYPE	BCW61A	BCW61B	BCW61C	BCW61D
Marking	BA	BB	BC	BD